











SN74LVC1G97

SCES416N - DECEMBER 2002 - REVISED JANUARY 2017

SN74LVC1G97 Configurable Multiple-Function Gate

Features

- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Supports Down Translation to V_{CC}
- Max t_{pd} of 6.3 ns at 3.3 V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Choose From Nine Specific Logic Functions

Applications

- **Barcode Scanners**
- Cable Solutions
- E-Books
- **Embedded PCs**
- Field Transmitter: Temperature or Pressure Sensors
- Fingerprint Biometrics
- HVAC: Heating, Ventilating, and Air Conditioning
- Network-Attached Storage (NAS)
- Server Motherboards and PSUs
- Software Defined Radios (SDR)
- TVs: High Definition (HDTV), LCD, and Digital
- Video Communications Systems
- Wireless Data Access Cards, Headsets, Keyboard, Mouse, and LAN Cards

3 Description

The SN74LVC1G97 device features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

This configurable multiple-function gate is designed for 1.65-V to 5.5-V V_{CC} operation.

This device functions as an independent gate, but because of Schmitt action, it may have different input threshold levels for positive-going (V_T+) and negativegoing (V_T) signals.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

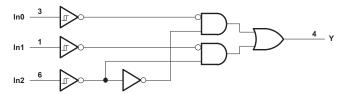
This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC1G97DBV	SOT-23 (6)	2.90 mm × 1.60 mm
SN74LVC1G97DCK	SC70 (6)	2.00 mm × 1.25 mm
SN74LVC1G97DRL		1.60 mm × 1.20 mm
SN74LVC1G97DRY	SOT (6)	1.45 mm × 1.00 mm
SN74LVC1G97DSF		1.00 mm × 1.00 mm
SN74LVC1G97YZP	DSBGA (6)	1.41 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)



Page



Table of Conten	ts
-----------------	----

1	Features 1	8.2 Functional B	ock Diagram
2	Applications 1	8.3 Feature Des	cription
3	Description 1	8.4 Device Func	tional Modes
4	Revision History2	9 Application and	Implementation 1
5	Pin Configuration and Functions	9.1 Application I	nformation1
6	Specifications4	9.2 Typical Appli	cation1
Ū	6.1 Absolute Maximum Ratings 4	10 Power Supply	Recommendations 12
	6.2 ESD Ratings	11 Layout	
	6.3 Recommended Operating Conditions	11.1 Layout Guid	delines 1
	6.4 Thermal Information	11.2 Layout Exa	mple 1:
	6.5 Electrical Characteristics	12 Device and Do	cumentation Support 14
	6.6 Switching Characteristics	12.1 Documenta	tion Support1
	6.7 Switching Characteristics	12.2 Receiving N	Notification of Documentation Updates 1
	6.8 Operating Characteristics	12.3 Community	Resources1
	6.9 Typical Characteristics	12.4 Trademarks	s 1 ₀
7	Parameter Measurement Information	12.5 Electrostati	Discharge Caution1
8	Detailed Description 8		ckaging, and Orderable
	8.1 Overview 8	Information	14

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

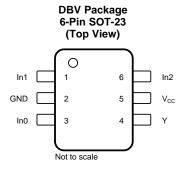
C	hanges from Revision M (June 2015) to Revision N	Page
•	Changed body size for SN74LVC1G97DRY to 1.45 mm × 1.00 mm	1
•	Changed body size for SN74LVC1G97DSF to 1.00 mm × 1.00 mm	1
•	Added Junction temperature, T _J in <i>Absolute Maximum Ratings</i>	4
•	Added Operating free-air temperature, T _A for BGA package in Recommended Operating Conditions	4
•	Added Receiving Notification of Documentation Updates section	14
_		

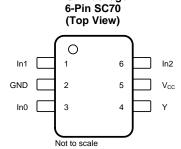
Changes from Revision L (December 2013) to Revision M

C	hanges from Revision K (October 2011) to Revision L			
•	Updated document to new TI data sheet format			
•	Removed Ordering Information table.			
•	Updated I _{off} in Features			
•	Updated operating temperature range.			

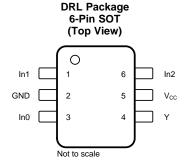


5 Pin Configuration and Functions

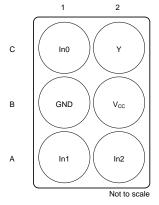




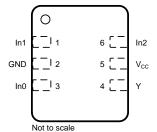
DCK Package



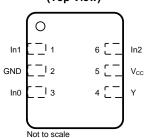
YZP Package 6-Pin DSBGA (Bottom View)



DRY Package 6-Pin SON (Top View)



DSF Package 6-Pin SON (Top View)



Pin Functions

PIN			I/O	DESCRIPTION					
NAME	DCT, DCU, DRY	YZP	1/0	DESCRIPTION					
In0	3	C1	I	Input 0					
ln1	1	A1	I	Input 1					
ln2	6	A2	I	Input 2					
GND	2	B1	_	Ground					
V _{CC}	5	B2	_	Power					
Υ	4	C2	0	Output					

Copyright © 2002–2017, Texas Instruments Incorporated



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage (2)		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impedance or power-off state (2)			6.5	V
Vo	Voltage applied to any output in the high or low state (2)(3)		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0 V		-50	mA
I _{OK}	Output clamp current	V _O < 0 V		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T_J	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

				VALUE	UNIT
,	V/ECD)	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
\		discharge	Charged device model (CDM), per JEDEC specification JESD22-C101\(^{2}\)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1)

			MIN	MAX	UNIT
V	Cumply yeltogo	Operating	1.65	5.5	V
V _{CC}	Supply voltage	Data retention only	1.5		V
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
	High-level output current	V _{CC} = 2.3 V		-8	mA
I _{OH}		V 0 V		-16	
		V _{CC} = 3 V		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I _{OL}	Low-level output current	V 0 V		16	mA
		V _{CC} = 3 V		24	
		V _{CC} = 4.5 V		32	
_	On exacting force air tensor exacting	BGA package	-40	85	°C
T _A	Operating free-air temperature	All other packages	-40	125	-0

All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See Implications of Slow or Floating CMOS Inputs, SCBA004.

Product Folder Links: SN74LVC1G97

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.4 Thermal Information

			SN74L\	VC1G97		
THERMAL METRIC ⁽¹⁾		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	YZP (DSBGA)	UNIT
		6 PINS	6 PINS	6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	165	259	142	123	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

		.,	-40°C	TO +85°C	-40°C		
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾ MAX	MIN	TYP ⁽¹⁾ MAX	UNIT
		1.65 V	0.79	1.16	0.79	1.16	
V_{T+}		2.3 V	1.11	1.56	1.11	1.56	
Positive-going input		3 V	1.5	1.87	1.5	1.87	V
threshold voltage		4.5 V	2.16	2.74	2.16	2.74	
		5.5 V	2.61	3.33	2.61	3.33	
		1.65 V	0.35	0.62	0.35	0.62	
V_{T-}		2.3 V	0.58	0.87	0.58	0.87	
Negative-going input		3 V	0.84	1.19	0.84	1.19	V
threshold voltage		4.5 V	1.41	1.9	1.41	1.9	
		5.5 V	1.87	2.29	1.87	2.29	
		1.65 V	0.3	0.62	0.3	0.62	
		2.3 V	0.4	0.8	0.4	0.8	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)		3 V	0.53	0.87	0.53	0.87	V
Tryotoroolo (V 4 V -)		4.5 V	0.71	1.04	0.71	1.04	
		5.5 V	0.71	1.11	0.71	1.11	
	$I_{OH} = -100 \ \mu A$	1.65 V to 5.5 V	$V_{CC} - 0.1$		$V_{CC} - 0.1$		V
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		1.2		
V_{OH}	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9		
VOH	I _{OH} = −16 mA	3 V	2.4		2.4		V
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		2.3		
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8		
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.1		0.1	
	I _{OL} = 4 mA	1.65 V		0.45		0.45	
V _{OL}	I _{OL} = 8 mA	2.3 V		0.3		0.3	V
VOL	I _{OL} = 16 mA	3 V		0.4		0.45	V
	I _{OL} = 24 mA	3 V		0.55		0.55	
	I _{OL} = 32 mA	4.5 V		0.55		0.58	
I _I	V _I = 5.5 V or GND	0 to 5.5 V		±5		±5	μΑ
l _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±10		±10	μΑ
I _{CC}	$V_I = 5.5 \text{ V or GND}, I_O = 0$	1.65 V to 5.5 V		10		10	μΑ
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V		500		500	μΑ
C _I	$V_I = V_{CC}$ or GND	3.3 V		3.5		3.5	pF

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

Product Folder Links: SN74LVC1G97



6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER			J (-40°C T	O 85°C				
		FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}		Any In	Y	3.2	14.4	2	8.3	1.5	6.3	1.1	5.1	ns

6.7 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

						-	-40°C T	O 125°C	;			
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t	d	Any In	Υ	3.2	16.4	2	9.3	1.5	7.3	1.1	6.1	ns

6.8 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	$V_{CC} = 3.3 \text{ V}$	V _{CC} = 5 V	UNIT	
PARAMETER		CONDITIONS	TYP	TYP	TYP	TYP	ONIT	
C_{pd}	Power dissipation capacitance	f = 10 MHz	22	23	23	26	pF	

6.9 Typical Characteristics

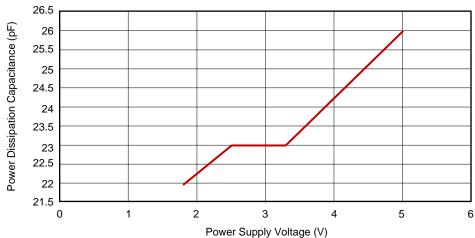


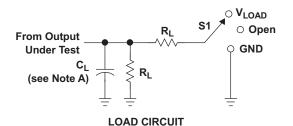
Figure 1. Power Dissipation Capacitance vs Power Supply Voltage

Submit Documentation Feedback

Copyright © 2002–2017, Texas Instruments Incorporated

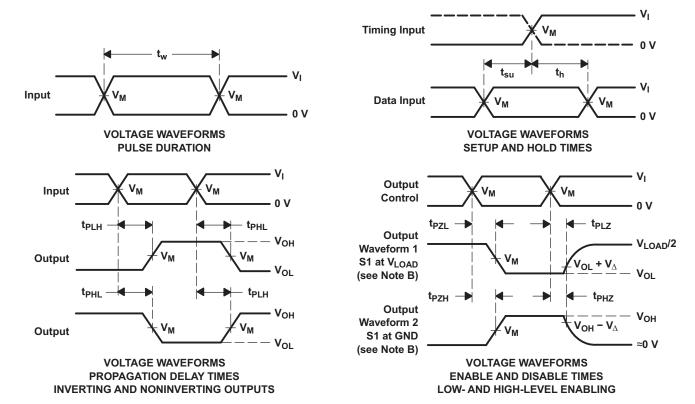


7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V_{LOAD}
t _{PHZ} /t _{PZH}	GND

.,	INF	PUTS	.,	.,		_	.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	$V_{\!\scriptscriptstyle \Delta}$
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V _{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z₀ = 50 W.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en}
- G. t_{PLH} and t_{PHL} are the same as t_{pd}
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms



8 Detailed Description

8.1 Overview

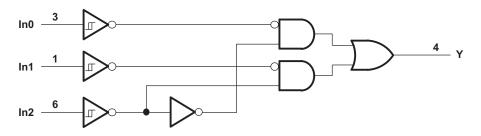
This configurable multiple-function gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G97 device features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose variations of common logic functions, like AND, OR, and NOT. All inputs can be connected to $V_{\rm CC}$ or GND.

This device functions as an independent gate, but because of Schmitt action, it may have different input threshold levels for positive-going $(V_{T_{+}})$ and negative-going $(V_{T_{-}})$ signals.

This device is fully-specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74LVC1G97 device has a wide operating V_{CC} range of 1.65 V to 5.5 V, which allows use in a broad range of systems. The 5.5-V I/Os allow down translation and also allow voltages at the inputs when $V_{CC} = 0$ V.

8.4 Device Functional Modes

Table 1 shows the functional modes of SN74LVC1G97.

Table 1. Function Table

	INPUTS	OUTPUT	
ln2	In1	In0	Υ
L	L	L	L
L	L	Н	L
L	Н	L	Н
L	Н	Н	Н
Н	L	L	L
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	Н



Table 2. Function Selection Table

LOGIC FUNCTION	FIGURE NUMBER
2-to-1 data selector	Figure 3
2-input AND gate	Figure 4
2-input OR gate with one inverted input	Figure 5
2-input NAND gate with one inverted input	Figure 5
2-input AND gate with one inverted input	Figure 6
2-input NOR gate with one inverted input	Figure 6
2-input OR gate	Figure 7
Inverter	Figure 8
Noninverted buffer	Figure 9

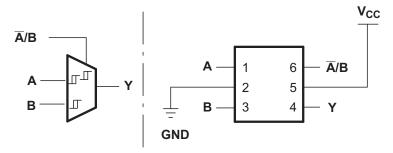


Figure 3. 2-to-1 Data Selector

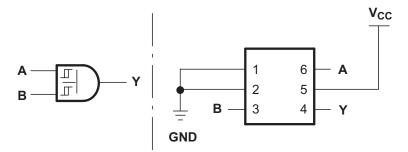


Figure 4. 2-Input AND Gate

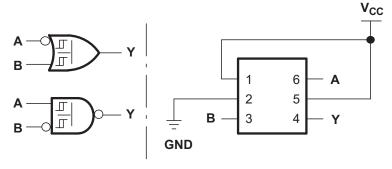


Figure 5. 2-Input OR Gate With One Inverted Input 2-Input NAND Gate With One Inverted Input

Copyright © 2002–2017, Texas Instruments Incorporated



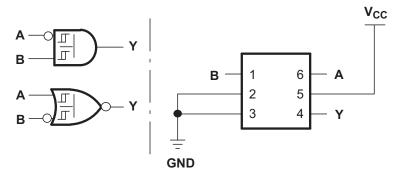


Figure 6. 2-Input AND Gate With One Inverted Input 2-Input NOR Gate With One Inverted Input

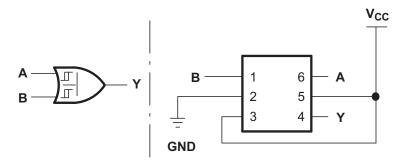


Figure 7. 2-Input OR Gate

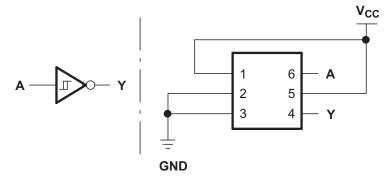


Figure 8. Inverter

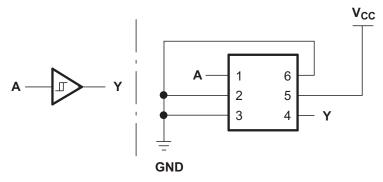


Figure 9. Noninverted Buffer



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Validate and test the design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC1G97 device offers flexible configuration for many design applications. This example describes basic power sequencing using the AND gate configuration. Power sequencing is often used in applications that require a processor or other delicate device with specific voltage timing requirements in order to protect the device from malfunctioning.

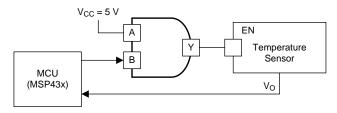


Figure 10. Simplified Application

9.2 Typical Application

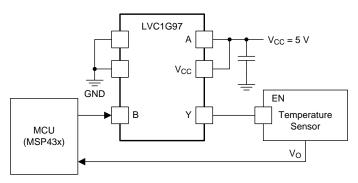


Figure 11. Typical Application

9.2.1 Design Requirements

- Recommended input conditions:
 - For rise time and fall time specifications, see $\Delta t/\Delta v$ in the Recommended Operating Conditions table.
 - For specified high and low levels, see V_{IH} and V_{IL} in the Recommended Operating Conditions table.
 - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5 V at any valid V_{CC}.
- Recommended output conditions:

Copyright © 2002-2017, Texas Instruments Incorporated

- Load currents must not exceed ±50 mA.
- Frequency selection criterion:
 - Figure 12 illustrates the effects of frequency on output current.
 - Added trace resistance and capacitance can reduce maximum frequency capability. Follow the layout practices listed in the *Layout* section.

Draduat Folder Links, CN7411



Typical Application (continued)

9.2.2 Detailed Design Procedure

The SN74LVC1G97 device uses CMOS technology and has balanced output drive. Avoid bus contentions that can drive currents that can exceed maximum limits.

The SN74LVC1G97 allows for performing logical Boolean functions with digital signals. Maintain input signals as close as possible to either 0 V or V_{CC} for optimal operation.

9.2.3 Application Curve

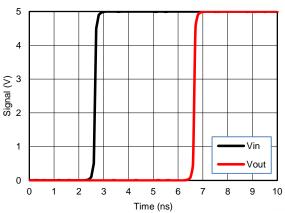


Figure 12. Simulated Input-to-Output Voltage Response Showing Propagation Delay at V_{CC} = 5 V

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions* table.

To prevent power disturbance, ensure good bypass capacitance for each V_{CC} terminal. For devices with a single-supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. Place the bypass capacitor as close to the power terminal as possible for best results.



11 Layout

11.1 Layout Guidelines

When using multiple-bit logic devices, inputs must never float.

In many cases, functions (or parts of functions) of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or when only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected, because the undefined voltages at the outside connections result in undefined operational states. Figure 13 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally they are tied to GND or $V_{\rm CC}$, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it disables the output section of the part when asserted, which does not disable the input section of the I/Os. Therefore, the I/Os cannot float when disabled.

11.2 Layout Example

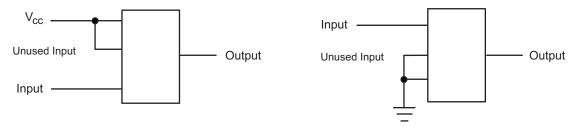


Figure 13. Layout Diagrams

Product Folder Links: SN74LVC1G97



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- Selecting the Right Texas Instruments Signal Switch, SZZA030

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

NanoFree, E2E are trademarks of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

Product Folder Links: SN74LVC1G97





19-Dec-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74LVC1G97DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C975 ~ C97K ~ C97R)	Samples
SN74LVC1G97DBVRE4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C975 ~ C97K ~ C97R)	Samples
SN74LVC1G97DBVRG4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C975 ~ C97K ~ C97R)	Samples
SN74LVC1G97DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C975 ~ C97K ~ C97R)	Samples
SN74LVC1G97DBVTG4	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C975 ~ C97K ~ C97R)	Samples
SN74LVC1G97DCKR	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS5 ~ CSF ~ CSK ~ CSR)	Samples
SN74LVC1G97DCKRE4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS5 ~ CSF ~ CSK ~ CSR)	Samples
SN74LVC1G97DCKRG4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS5 ~ CSF ~ CSK ~ CSR)	Samples
SN74LVC1G97DCKT	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS5 ~ CSF ~ CSK ~ CSR)	Samples
SN74LVC1G97DCKTG4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS5 ~ CSF ~ CSK ~ CSR)	Samples
SN74LVC1G97DRLR	ACTIVE	SOT	DRL	6	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS7 ~ CSR)	Samples
SN74LVC1G97DRLRG4	ACTIVE	SOT	DRL	6	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CS7 ~ CSR)	Samples
SN74LVC1G97DRYR	ACTIVE	SON	DRY	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CS	Samples
SN74LVC1G97DSFR	ACTIVE	SON	DSF	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CS	Samples
SN74LVC1G97YZPR	ACTIVE	DSBGA	YZP	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CSN	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PACKAGE OPTION ADDENDUM



19-Dec-2016

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G97:

Automotive: SN74LVC1G97-Q1

Enhanced Product: SN74LVC1G97-EP

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



www.ti.com

PACKAGE OPTION ADDENDUM

19-Dec-2016

• Enhanced Product - Supports Defense, Aerospace and Medical Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 19-Dec-2016

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G97DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G97DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G97DCKR	SC70	DCK	6	3000	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
SN74LVC1G97DCKR	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G97DCKT	SC70	DCK	6	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G97DCKT	SC70	DCK	6	250	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
SN74LVC1G97DCKT	SC70	DCK	6	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G97DRLR	SOT	DRL	6	4000	180.0	9.5	1.78	1.78	0.69	4.0	8.0	Q3
SN74LVC1G97DRLR	SOT	DRL	6	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G97DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G97DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G97YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

www.ti.com 19-Dec-2016

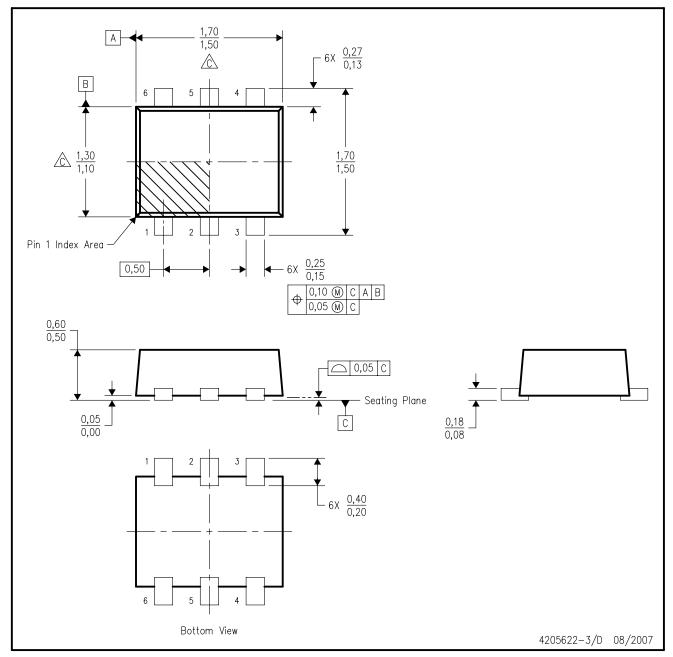


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G97DBVR	SOT-23	DBV	6	3000	202.0	201.0	28.0
SN74LVC1G97DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1G97DCKR	SC70	DCK	6	3000	205.0	200.0	33.0
SN74LVC1G97DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1G97DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC1G97DCKT	SC70	DCK	6	250	205.0	200.0	33.0
SN74LVC1G97DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC1G97DRLR	SOT	DRL	6	4000	184.0	184.0	19.0
SN74LVC1G97DRLR	SOT	DRL	6	4000	202.0	201.0	28.0
SN74LVC1G97DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G97DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G97YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0

DRL (R-PDSO-N6)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body dimensions do not include mold flash, interlead flash, protrusions, or gate burrs.

 Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0,15 per end or side.
- D. JEDEC package registration is pending.



DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. SON (Small Outline No-Lead) package configuration.
- The exposed lead frame feature on side of package may or may not be present due to alternative lead frame designs.
- E. This package complies to JEDEC MO-287 variation UFAD.
- $frac{f}{K}$ See the additional figure in the Product Data Sheet for details regarding the pin 1 identifier shape.





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

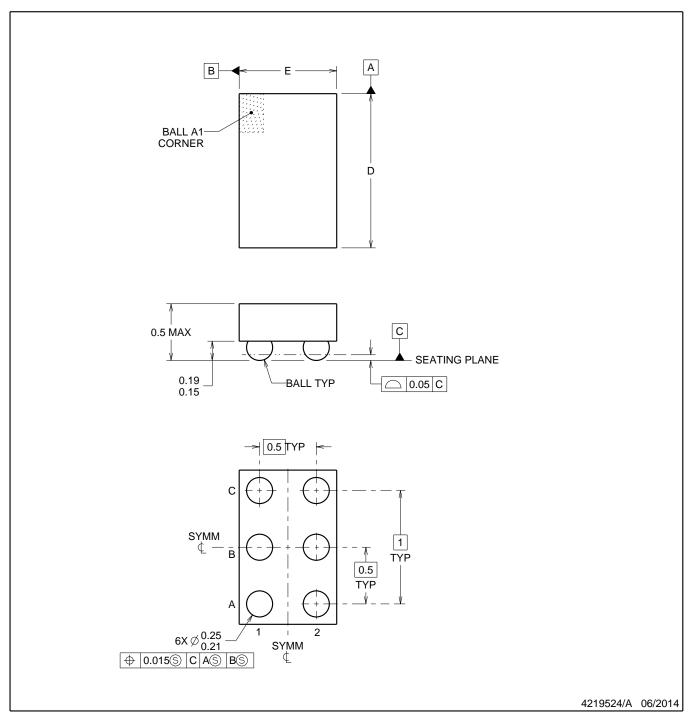
 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.





DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



IMPORTANT NOTICE FOR TI DESIGN INFORMATION AND RESOURCES

Texas Instruments Incorporated ('TI") technical, application or other design advice, services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using any particular TI Resource in any way, you (individually or, if you are acting on behalf of a company, your company) agree to use it solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources.

You understand and agree that you remain responsible for using your independent analysis, evaluation and judgment in designing your applications and that you have full and exclusive responsibility to assure the safety of your applications and compliance of your applications (and of all TI products used in or for your applications) with all applicable regulations, laws and other applicable requirements. You represent that, with respect to your applications, you have all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. You agree that prior to using or distributing any applications that include TI products, you will thoroughly test such applications and the functionality of such TI products as used in such applications. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

You are authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING TI RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY YOU AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

You agree to fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of your non-compliance with the terms and provisions of this Notice.

This Notice applies to TI Resources. Additional terms apply to the use and purchase of certain types of materials, TI products and services. These include; without limitation, TI's standard terms for semiconductor products http://www.ti.com/sc/docs/stdterms.htm), evaluation modules, and samples (http://www.ti.com/sc/docs/sampterms.htm).

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2017, Texas Instruments Incorporated